

L Number	Hits	Search Text	DB	Time stamp
1	270109	carrier near3 capture near3 layer near3 spacer	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/01 05:07
2	0	carrier near3 capture near3 layer near3 spacer	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/01 05:07
3	0	carrier near3 capture near3 layer same spacer	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/01 05:07
4	24	carrier near3 capture near3 layer	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/01 05:07
5	1	(carrier near3 capture near3 layer ) and spacer near3 layer	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/01 05:08
6	6	(carrier near3 capture near3 layer ) and spacer	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/01 05:13
7	297	fresnel near3 lens same mode	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/01 05:13
8	30	fresnel near3 lens near3 mode	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/01 05:13
-	62	laser near3 diode and bleach\$3 near3 absorb\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/31 16:44
-	45	laser near3 diode and bleach\$3 near3 absorb\$4 and shap\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/31 17:28
-	5	laser near3 diode\$1 and ((bleach\$3 or decolor\$3) near3 absorb\$4) and ingaas and vertical	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/31 17:13
-	0	laser near3 diode\$1 and bleach\$3 near3 absorb\$4 and current near3 constrict\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/31 17:29
-	0	laser near3 diode\$1 and bleach\$3 near3 absorb\$4 and current near3 block\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/31 17:29
-	0	laser near3 diode\$1 and bleach\$3 near3 absorb\$4 and current near3 oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/31 17:30
-	5	laser near3 diode\$1 and bleach\$3 near3 absorb\$4 and (vertical near3 (cavity or resonator))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/31 17:35
-	1262	laser near3 diode\$1 and bleach\$3 near3 layer	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/31 17:35

-	64	laser near3 diode\$1 and bleach\$3 near3 layer	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/31 17:38
-	2	((laser near3 diode\$1 and bleach\$3 near3 layer ) and 372/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/31 17:37
-	138	((laser near3 diode\$1 or (semiconductor near3 laser)) and bleach\$3 near3 absor\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/31 17:39
-	44	((laser near3 diode\$1 or (semiconductor near3 laser)) and bleach\$3 near3 absor\$6 ) and 372/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/31 17:55
-	29	((laser near3 diode\$1) same (saturable near3 absorb\$4)) and (bleach\$3 or transparent) and ingaas	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/31 17:59
-	9	((laser near3 diode\$1) same (saturable near3 absorb\$4)) and bleach\$3 and ingaas	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/31 18:05
-	10	(bragg or dbr) and ((saturable near3 absorb\$4) same bleach\$3) and ingaas	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/31 18:08
-	23	(bragg or dbr) and ((saturable near3 absorb\$4) same bleach\$3) and laser near3 diode\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/31 18:10
-	0	(bragg or dbr) and ((saturable near3 absorb\$4) same bleach\$3) and surfage near3 emit\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/31 18:10
-	3	(bragg or dbr) and ((saturable near3 absorb\$4) same bleach\$3) and surface near3 emit\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/31 18:11
-	1	((saturable near3 absorb\$4) same bleach\$3) and 372/50.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/31 18:11
-	3	((saturable near3 absorb\$4) and bleach\$3) and 372/50.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/31 18:29
-	8	((saturable near3 absorb\$4) and bleach\$3) and (vertical near3 cavity or resonator))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/31 18:13
-	0	((saturable near3 absorb\$4) and bleach\$3) and 372/96.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/31 18:29
-	41	(saturable near3 absorb\$4) and 372/96.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/31 18:31
-	0	(saturable near3 absorb\$4 near3 ingaas) and 372/96.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/31 18:30
-	3	((saturable near3 absorb\$4) same (bleach\$3 or transparent)) and 372/96.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/31 18:32

-	0	((saturable near3 absorb\$4) near3 (bleach\$3 or transparent)) and 372/96.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/31 18:33
-	393	(material near3 wavelength) same quarter	USPAT; US-PGPUB	2004/05/31 20:07
-	497	"171" and 372/\$.ccls.	USPAT; US-PGPUB	2004/05/31 19:44
-	59	((material near3 wavelength) same quarter) and 372/\$.ccls.	USPAT; US-PGPUB	2004/05/31 19:50
-	41	((material near3 wavelength) same quarter) and absorb\$3 near3 layer	USPAT; US-PGPUB	2004/05/31 19:51
-	0	((material near3 wavelength) same quarter) and absorb\$3 near3 bleach\$3	USPAT; US-PGPUB	2004/05/31 19:51
-	0	((material near3 wavelength) same quarter) and absorb\$3 same bleach\$3	USPAT; US-PGPUB	2004/05/31 19:51
-	7	((material near3 wavelength) same quarter) and absorb\$ near3 quantum	USPAT; US-PGPUB	2004/05/31 19:53
-	45	((material near3 wavelength) same quarter) and quantum near3 well	USPAT; US-PGPUB	2004/05/31 19:53
-	32	((material near3 wavelength) same quarter) and quantum near3 well and absor\$6	USPAT; US-PGPUB	2004/05/31 19:54
-	32	((material near3 wavelength) same quarter) and quantum near3 well and absor\$8	USPAT; US-PGPUB	2004/05/31 19:56
-	24	((material near3 wavelength) same quarter) and quantum near3 well and absor\$8 and thickness	USPAT; US-PGPUB	2004/05/31 19:59
-	3	((material near3 wavelength) same quarter) and saturable near3 absor\$8 and thickness	USPAT; US-PGPUB	2004/05/31 20:00
-	13	(material near3 wavelength) same quarter same (quantum near3 well\$1)	USPAT; US-PGPUB	2004/05/31 20:12
-	48	(wavelength near3 quarter near3 thickness) same (quantum near3 well\$1)	USPAT; US-PGPUB	2004/05/31 20:25
-	314	ion near3 implantation same proton	USPAT; US-PGPUB	2004/05/31 20:26
-	160	ion near3 implantation near3 proton	USPAT; US-PGPUB	2004/05/31 20:26